

SOT-23 Plastic-Encapsulate Diodes

DAP202

SWITCHING DIODE

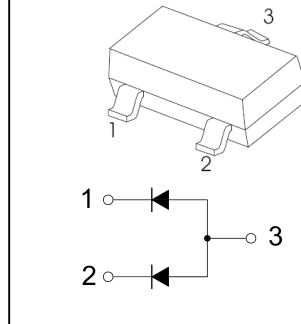
FEATURES

- High Speed
- High Reliability
- Suitable for High Packing Density Layout

APPLICATIONS

- High Speed Switching

SOT-23



MARKING: P

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	80	V
I_O	Continuous Forward Current	100	mA
I_{FM}	Peak Forward Current	300	mA
I_{SM}	Surge Current	4	A
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	80			V
Reverse current	I_R	$V_R=70\text{V}$			0.1	μA
Forward voltage	V_F	$I_F=100\text{mA}$			1.2	V
Total capacitance	C_{tot}	$V_R=6\text{V}, f=1\text{MHz}$			3.5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=5\text{mA}, V_R=6\text{V}$			4	ns

Typical Characteristics

DAP202

